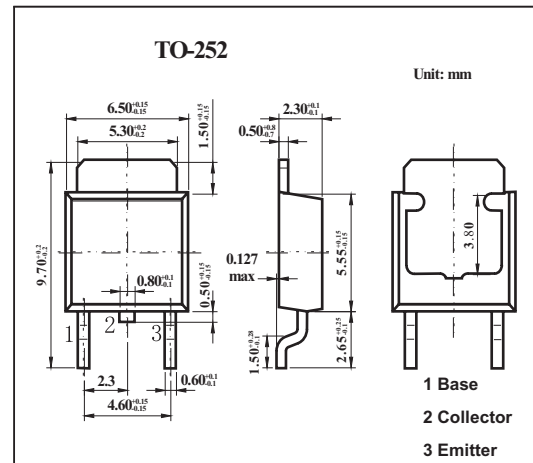


Silicon PNP Transistor

2SA1923

■ Features

- High Voltage: $V_{CB0} = -400V$
- Low Saturation Voltage: $V_{CE(sat)} = -1V(\text{Max.})$
 $I_C = -100mA, I_B = -10mA$

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-to-Base Voltage	V_{CB0}	-400	V
Collector-to-Emitter Voltage	V_{CEO}	-400	V
Emitter-to-Base Voltage	V_{EBO}	-7	V
Collector Current	I_C	-0.5	A
Collector Current (Pulse)	I_{CP}	-1	A
Base Current	I_B	-0.25	A
Collector Dissipation $T_c = 25^\circ C$	P_C	1	W
		10	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to 150	$^\circ C$

2SA1923

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit	
Collector Cutoff Current	ICBO	V _{CB} =-400V, I _E =0			-10	μA	
Emitter Cutoff Current	IEBO	V _{EB} =-7V, I _C =0			-1	μA	
Collector-to-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =-10mA, I _B =0	-400			V	
DC Current Gain	h _{FE}	V _{CE} =-5V, I _C =-20mA	140		450		
		V _{CE} =-5V, I _C =-100mA	140		400		
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =-100mA, I _B =-10mA		-0.4	-1.0	V	
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =-100mA, I _B =-10mA		-0.76	-0.9	V	
Transition Frequency	f _T	V _{CE} =-5V, I _C =-50mA		35		MHz	
Collector Output Capacitance	C _{ob}	V _{CB} =-10V, f=1MHz, I _E =0		18		pF	
Switching Time Turn-on Time	t _{on}	<p> $20\ \mu\text{s}$ INPUT I_{B1} OUTPUT I_{B2} I_{B2} $2\text{k}\Omega$ $V_{CC} = -200\text{V}$ $I_{B1} = 10\text{mA}$, $I_{B2} = 20\text{mA}$, DUTY CYCLE $\leq 1\%$ </p>		0.2		μs	
Switching Time Storage Time	t _{stg}				2.3		μs
Switching Time Fall Time	t _f				0.2		μs